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Contents

vii *Conference Committee*

MATERIALS FOR HIGH NA EUV LITHOGRAPHY

12498 06 **Advanced development methods for high-NA EUV lithography** [12498-4]

12498 07 **Development on main chain scission resists for high-NA EUV lithography** [12498-5]

PROCESS IMPROVEMENTS

12498 0A **Continued optimization of point-of-use filtration for metal oxide photoresists to reduce defect density** [12498-8]

12498 0B **Development of a novel cleaner for contaminant removal in equipment used in semiconductor manufacturing which reduces time and solvent waste** [12498-9]

12498 0C **Modification of organic underlayers by plasma during dry etching and its effect on the film properties** [12498-10]

EUVL STOCHASTICS: JOINT SESSION WITH 12494 AND 12498

12498 0D **A novel formulated developer for negative-tone imaging with EUV exposure to improve chemical stochastic** [12498-11]

12498 0E **Towards molecular-scale kinetic Monte Carlo simulation of pattern formation in photoresist materials for EUV nanolithography** [12498-12]

12498 0F **Photoresists with precisely controlled molecular weight, composition, and sequence** [12498-13]

RESISTS FUNDAMENTALS I

12498 0I **Effects of photoacid generator decomposition on dissolution kinetics of poly(4-hydroxystyrene) in tetraalkylammonium hydroxide aqueous solutions** [12498-16]

12498 0J **Mean free path of electrons in EUV photoresist in the energy range 20 to 450 eV** [12498-17]

12498 0M **Role of counter-anion chemistry, free volume, and reaction byproducts in chemically amplified resists** [12498-20]

UNDERLAYERS AND TOP COATS

- 12498 ON **Novel assist layers to enhance EUV lithography performance of photoresists on different substrates** [12498-21]
- 12498 OO **New functional surface treatment process and primers for high-NA EUV lithography** [12498-22]
- 12498 OQ **Chemical trimming overcoat: an advanced spin-on process for photoresist enhancement in EUV lithography** [12498-24]
- 12498 OR **Scaled-down deposited underlayers for EUV lithography** [12498-73]

RESISTS FUNDAMENTALS II

- 12498 OS **Dissociative photoionization of EUV lithography photoresist models** [12498-26]
- 12498 OT **EUV-induced activation mechanism of photoacid generators: key factors affecting EUV sensitivity** [12498-27]
- 12498 OU **Fundamental studies of interactions between polymer substrate and precursor in sequential infiltration synthesis** [12498-28]
- 12498 OW **A scientific framework for establishing ultrafast molecular dynamic research in imec's Attolab** [12498-30]

NON CHEMICALLY AMPLIFIED RESISTS FOR EUV LITHOGRAPHY I

- 12498 OX **Enhancing the sensitivity of a high resolution negative-tone metal organic photoresist for extreme ultra violet lithography** [12498-31]
- 12498 OZ **Influence of the anion in tin-based EUV photoresists properties** [12498-33]
- 12498 11 **Indium nitrate hydrate films as EUV resists by evaluating with 92-eV electron beam** [12498-35]

NON CHEMICALLY AMPLIFIED RESISTS FOR EUV LITHOGRAPHY II

- 12498 12 **EUV lithography patterning using multi-trigger resist** [12498-36]
- 12498 13 **Negative-tone resists for EUV lithography** [12498-37]
- 12498 14 **Single-component silicon-based patterning materials for EUV lithography** [12498-38]

- 12498 15 **Potential of biomass EUV non-CAR type resist for high-NA EUV lithography** [12498-39]
- 12498 16 **Fluoroalkylated tin-oxo nano clusters as resist candidates for extreme UV lithography** [12498-40]

NOVEL PATTERNING MATERIALS

- 12498 17 **Sequence-defined polypeptoid CARs for electron-beam and EUV lithography** [12498-41]
- 12498 18 **Chitosan as a water-based photoresist for DUV lithography** [12498-42]
- 12498 19 **Micro-nanostructuring by optical lithography and nitridation of photo-patternable TiO₂ sol-gel to obtain micro-nanostructured TiN** [12498-43]
- 12498 1B **Molecular layer deposition of an Al-based hybrid resist for electron-beam and EUV lithography** [12498-45]
- 12498 1C **The novel materials for pattern growing on EUV resists** [12498-46]

POSTER SESSION

- 12498 1D **Metal purifier for TMAH developer solution** [12498-47]
- 12498 1E **Fundamentals of EUV stack for improving patterning performance** [12498-49]
- 12498 1F **Establishment of new process technology for EUV lithography** [12498-50]
- 12498 1G **Recent advances in EUV patterning in preparation towards high-NA EUV** [12498-51]
- 12498 1H **Novel UPE filtration technology for advanced photolithography materials** [12498-53]
- 12498 1J **Profile control in conductor metal wet etch with advanced photoresists** [12498-55]
- 12498 1K **Positive tone i-line photoresist with controlled undercut profile for advanced packaging** [12498-56]
- 12498 1L **Metallic contamination reduction in polymer solution using membrane purification technology** [12498-57]
- 12498 1M **Thin underlayer materials for metal oxide resist patterning** [12498-58]
- 12498 1N **Use of highly EUV absorbing element in chemically amplified resist** [12498-59]

- 12498 1O **Design concept of a positive tone organometal chemically amplified resist to enhance the sensitivity and etching durability for high resolution EUV single patterning** [12498-60]
- 12498 1R **Novel polymer design for ultra-low stress material for advanced packaging applications** [12498-63]
- 12498 1S **Electron beam and optical patterning of polymerizable ionic liquid-based resists** [12498-65]
- 12498 1T **Ultra-high carbon fullerene-based spin-on-carbon hardmasks** [12498-66]
- 12498 1U **Predicting the critical features of the chemically-amplified resist profile based on machine learning** [12498-67]
- 12498 1V **Considerations in the design of photoacid generators** [12498-68]
- 12498 1W **Spin speed impact on photoresist thin film properties and EUV lithographic performance** [12498-69]
- 12498 1Y **Defectivity reduction in EUV resists through novel high-performance Point-Of-Use (POU) filters** [12498-74]
- 12498 21 **Coater/developer-based techniques to achieve tight pitches towards high-NA EUV** [12498-80]
- 12498 22 **Optimization of spin-on metal oxide resist performance via new development techniques on sub-30nm pitch patterning** [12498-81]
- 12498 25 **Chemical information extraction from scanning electron microscopy images on the basis of image recognition** [12498-97]
- 12498 26 **Reaction mechanisms and EB patterning evaluation of Sn-complex-side-chain polymer used for EUV lithography** [12498-99]
- 12498 27 **Study on irradiation effects by femtosecond-pulsed extreme ultraviolet in resist materials** [12498-100]
- 12498 29 **Dependence of swelling and dissolution kinetics of poly(4-hydroxystyrene) in alkaline aqueous solution on alkyl chain length of tetraalkylammonium hydroxide** [12498-104]